Degenerate N Doping Of Few Layer Transition Metal

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Degenerate N Doping Of Few

We report here the first degenerate n-doping of few-layer MoS2 and WSe2 semiconductors by surface charge transfer using potassium. High-electron sheet densities of ~1.0 × 1013 cm–2 and 2.5 × 1012 cm–2 for MoS2 and WSe2 are obtained, respectively.

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Figure 2 from Degenerate n-doping of few-layer transition ...
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Literature Review: Degenerate n-Doping of Few-Layer Transition Metal Dichalcogenides by Potassium July 29, 2015 July 29, 2015 / druffeldan The article I am reviewing is called “Degenerate n-Doping of Few-Layer Transition Metal Dichalcogenides by Potassium” (full citation below).

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CiteSeerX - Document Details (Isaac Councill, Lee Giles, Pradeep Teregowda): ABSTRACT: We report here the first degenerate n-doping of few-layer MoS 2 and WSe 2 semiconductors by surface charge transfer using potassium. High-electron sheet densities of ~1.0 × 10 13 cm −2 and 2.5 × 10 12 cm −2 for MoS 2 and WSe 2 are obtained, respectively.

Letter pubs.acs.org/NanoLett Degenerate n-Doping of Few ...

Recently, molecular dopants consisting of dimers of either 19-electron sandwich compound or of organic radicals have been reported to possess moderate air-stability and can effectively realize n-doping in organic semiconductors, as well as surfaces and low-dimensional materials , , , , , , including few-layer TMDCs , , . However, to date the use of dimers to dope TMDCs have been limited to solution processing, in which the interfaces established are not sufficiently clean to understand the ...

Degenerate electron-doping in two-dimensional tungsten ...

A degenerate semiconductor is a semiconductor with such a high level of doping that the material starts to act more like a metal than as a semiconductor. Unlike non-degenerate semiconductors, these kind of semiconductor do not obey law of mass action, which relates intrinsic carrier concentration with temperature and bandgap.

Degenerate semiconductor - Wikipedia

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Degenerate N Doping Of Few Layer Transition Metal

Degenerate n-Doping of Few-Layer Transition Metal Dichalcogenides by Potassium.

Degenerate n-Doping of Few-Layer Transition Metal ...

The n-doped samples exhibit excellent stability in both ambient air and vacuum. Notably, we obtained a high electron sheet density of ~1.2 × 10(13) cm(-2), which corresponds to the degenerate doping limit for MoS2.

Air-stable surface charge transfer doping of MoS_2 by ...

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n- or p-type doping of some TMDs can be carried out by decorating with substances with ultra low or high work function. For instance, degenerate n-doping of few-layer WSe 2 and MoS 2 was performed by surface charge transfer using potassium [29]. Also, transition metal oxides such as MoO 3−x [30] and WO 3−x [31],

Reversible electron doping in monolayer WS2 via a chemical ...

Furthermore, n-type doping in the Ti–WSe 2 FET shows weak degenerate behaviour whereas for Co and Pt contacts, it was possible to modulate the total carrier concentration by gate bias owing to higher barrier height for electron conduction.

Non-degenerate n-type doping by hydrazine treatment in ...

Further, several doping mechanisms on MoS 2 have produced degenerate doping, which leads to MoS 2 behaving like a metal with the resultant Fermi level close to the edge of the conduction band (or valence band).9 Although degenerate doping is important to tune the Schottky barrier with metal contacts,9 nondegenerate doping

Interfacial Nondegenerate Doping of MoS2 and Other Two

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Even degenerate levels of doping imply low concentrations of impurities with respect to the base semiconductor. In intrinsic crystalline silicon, there are approximately 5×1022atoms/cm3. Doping concentration for silicon semiconductors may range anywhere from 1013cm−3to 1018cm−3.